NSN 5961-01-044-2670

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View Online at https://aerobasegroup.com/nsn/5961-01-044-2670 **Inclosure Material:** Metal all transistor **Overall Length:** 0.120 inches all transistor and 0.140 inches all transistor **Terminal Length:** 0.500 inches all transistor **Overall Diameter:** 0.192 inches all transistor and 0.222 inches all transistor **Internal Configuration:** Junction contact all transistor Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-106 all transistor **Internal Junction Configuration:** Pnp all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Terminal all transistor **Terminal Circle Diameter:** 0.095 inches all transistor and 0.105 inches all transistor **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: -12.0 breakdown voltage, collector-to-emitter, base open all transistor **Current Rating Per Characteristic:** -80.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 200.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction all transistor **Terminal Type And Quantity:** 4 uninsulated wire lead all transistor Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No

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